

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)TYP}$	I_D
40V	$1.2m\Omega@10V$	260A



合肥矽普半导体

Siliup Semiconductor Technology Co., Ltd

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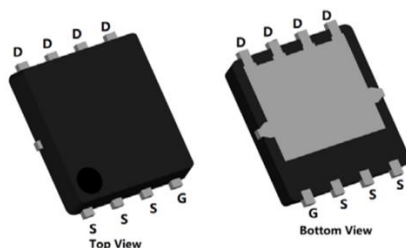
Feature

- Fast Switching
- Low Gate Charge and $R_{DS(on)}$
- **AEC-Q101** qualified
- Advanced Split Gate Trench Technology
- **100% UIS TESTED**
- **100% ΔV_{ds} TESTED**

Applications

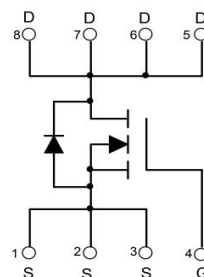
- DC-DC Converters
- Power management functions
- Synchronous-rectification applications

Package



PDFN5X6-8L

Circuit diagram



Marking



40N01BGHPA :Device Code
** :Week Code

Order Information

Device	Package	Unit/Tape
SP40N01BGHNPA	PDFN5X6-8L	5000

Absolute maximum ratings (Ta=25°C, unless otherwise noted)

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V _{DSS}	40	V
Gate-Source Voltage	V _{GSS}	±20	V
Continuous Drain Current (Tc=25°C)	I _D	260	A
Continuous Drain Current (Tc=100°C)	I _D	173	A
Pulse Drain Current Tested	I _{DM}	1040	A
Single pulsed avalanche energy ¹	E _{AS}	930	mJ
Power Dissipation (Tc=25°C)	P _D	168	W
Power Dissipation (Tc=100°C)	P _D	84	W
Thermal Resistance Junction-to-Case	R _{θJC}	0.89	°C/W
Thermal Resistance Junction-to-Ambient	R _{θJA}	54	°C/W
Storage Temperature Range	T _{STG}	-55 to 175	°C
Operating Junction Temperature Range	T _J	-55 to 175	°C

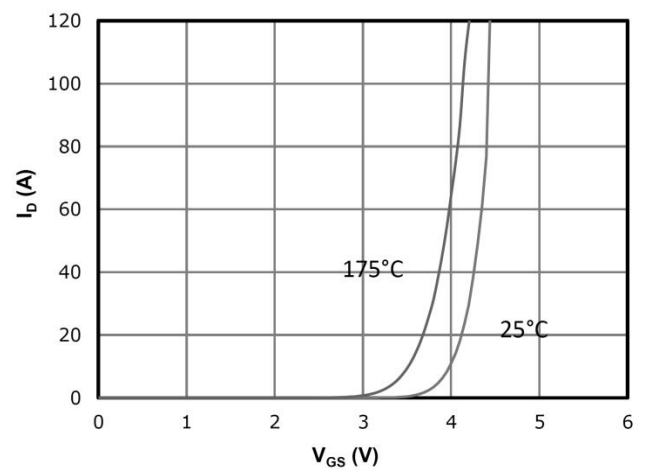
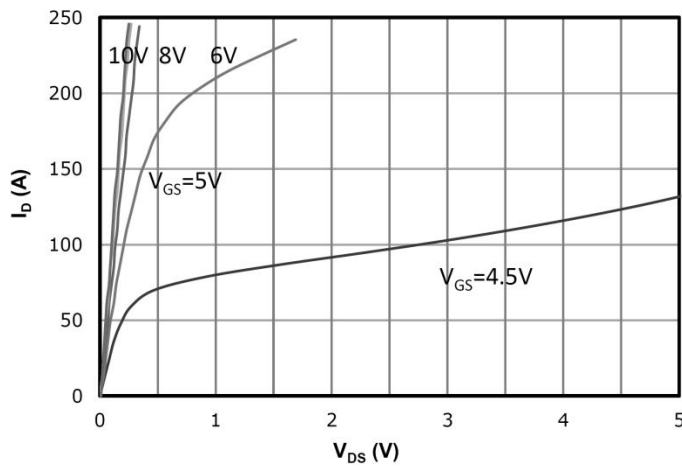
Electrical characteristics (Ta=25°C, unless otherwise noted)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	VGS=0V , ID=250uA	40	45	-	V
Drain-Source Leakage Current	IDSS	VDS=40V , VGS=0V , TJ=25℃	-	-	1	uA
Gate-Source Leakage Current	IGSS	VGS=±20V , VDS=0V	-	-	±100	nA
Gate Threshold Voltage	VGS(th)	VGS=VDS , ID=250uA	2.5	3.0	3.5	V
Static Drain-Source On-Resistance	RDS(ON)	VGS=10V , ID=75A	-	1.2	1.5	mΩ
Gate Resistance	RG	VDS=20V , VGS=0V , f=1MHz	-	2.55	-	Ω
Dynamic characteristics						
Input Capacitance	Ciss	VDS=20V , VGS=0V , f=1MHz	-	5014	-	pF
Output Capacitance	Coss		-	1478	-	
Reverse Transfer Capacitance	Crss		-	126	-	
Total Gate Charge	Qg	VDS=20V , VGS=10V , ID=150A	-	72	-	nC
Gate-Source Charge	Qgs		-	24	-	
Gate-Drain Charge	Qgd		-	15.4	-	
Gate Plateau Voltage	Vplateau		-	4.8	-	V
Switching Characteristics						
Turn-On Delay Time	Td(on)	VDD=20V , VGS=10V , RG=5Ω , ID=75A	-	12	-	nS
Rise Time	Tr		-	81	-	
Turn-Off Delay Time	Td(off)		-	25	-	
Fall Time	Tf		-	24	-	
Diode Characteristics						
Diode Forward Voltage	VSD	VGS=0V , IS=1A , TJ=25℃	-	-	1.2	V
Diode Continuous Current	Is		-	-	260	A
Reverse recover time	Trr	IS=50A , di/dt=100A/us , TJ=25℃	-	90	-	nS
Reverse recovery charge	Qrr		-	200	-	nC

Note :

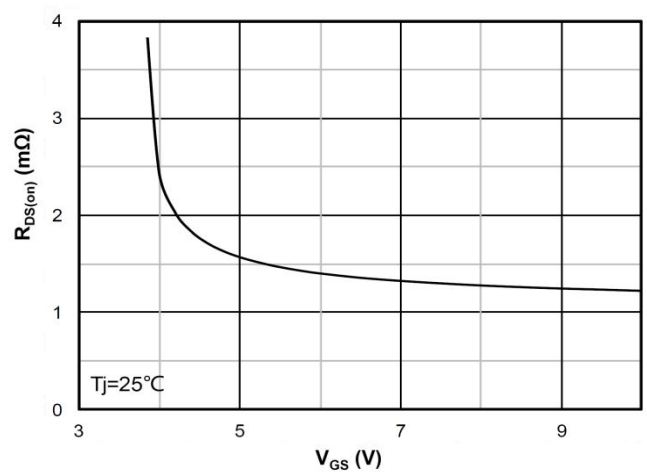
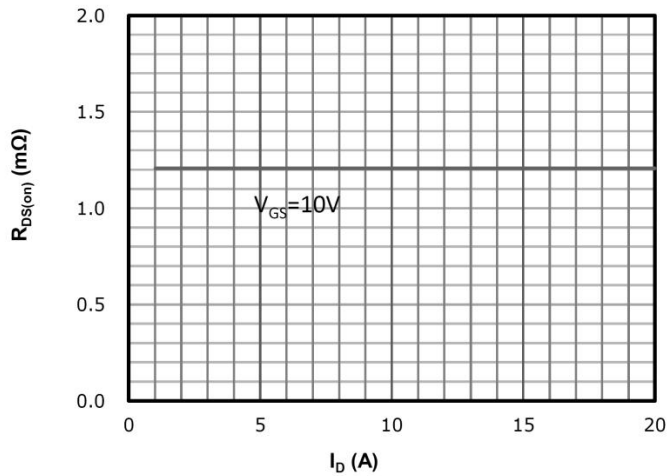
- The test condition is V_{DD}=20V, V_{GS}=10V, L=0.5mH, R_G=25Ω;

Typical Characteristics



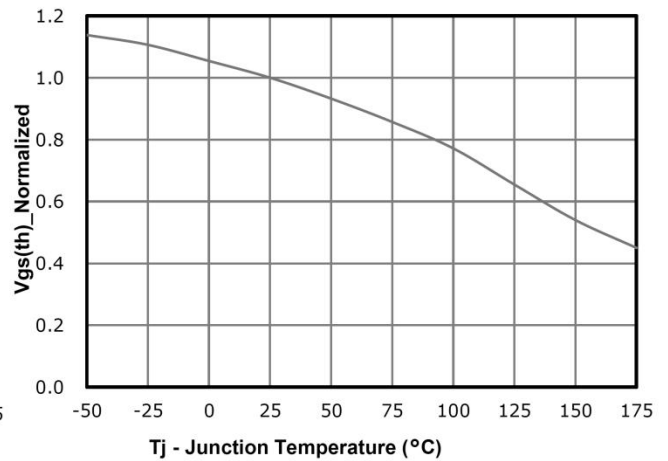
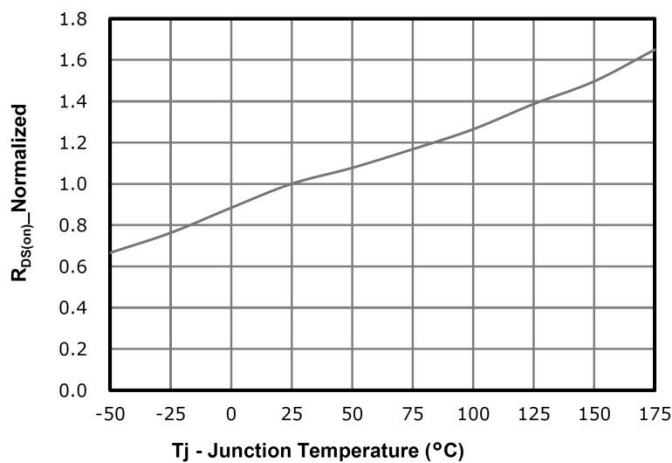
Output Characteristics

Transfer Characteristics



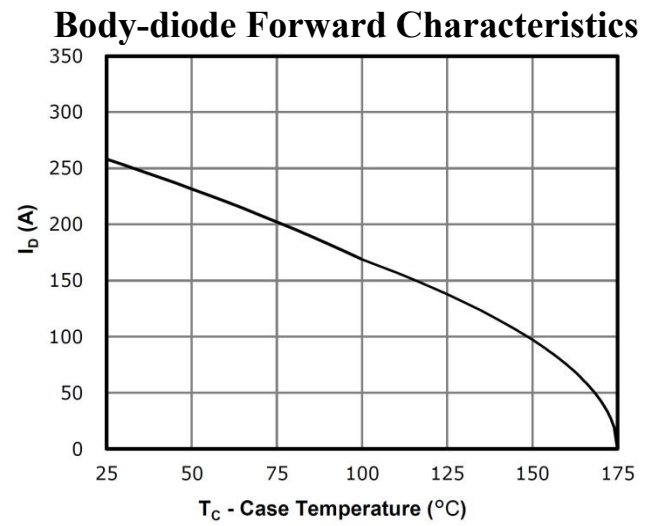
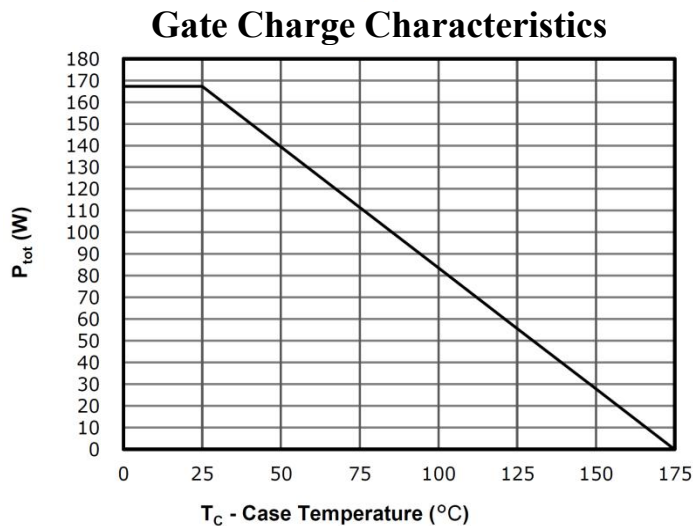
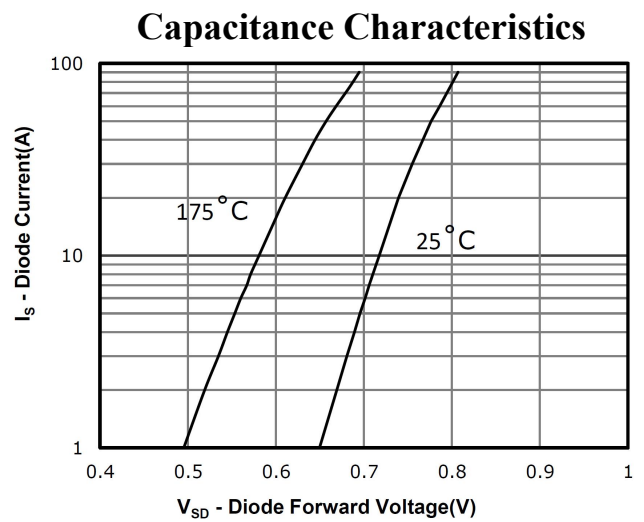
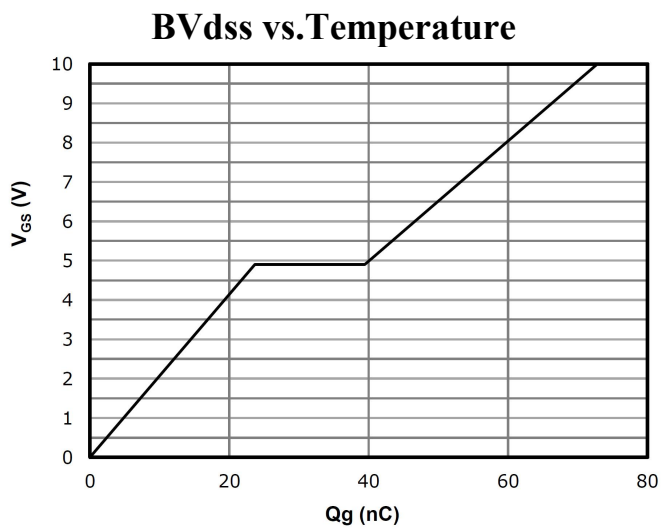
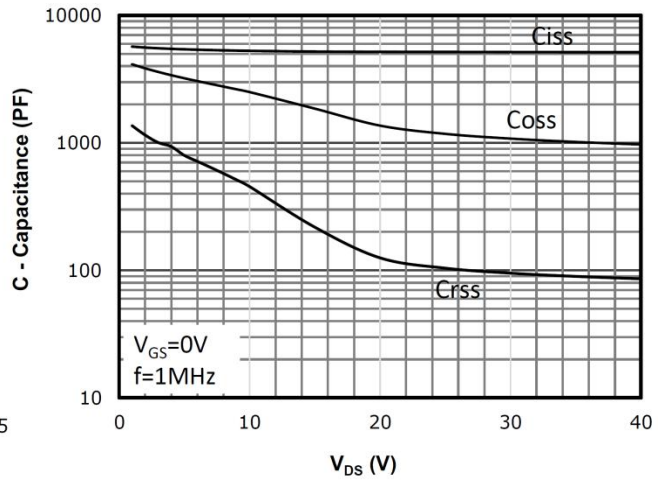
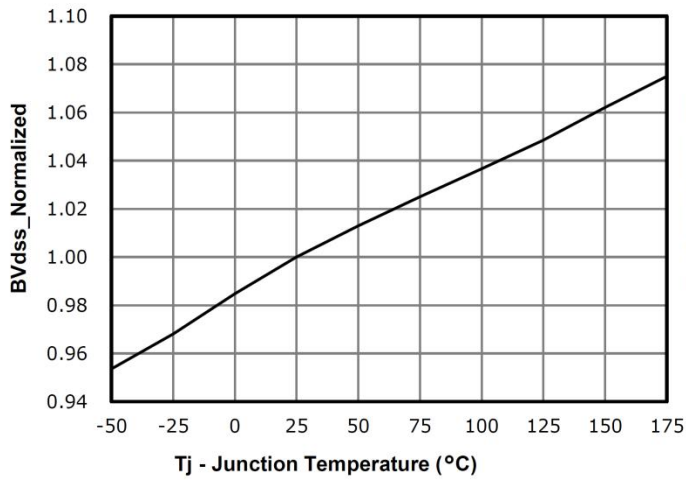
$R_{DS(on)}$ vs Drain Current

$R_{DS(on)}$ vs Gate Voltage



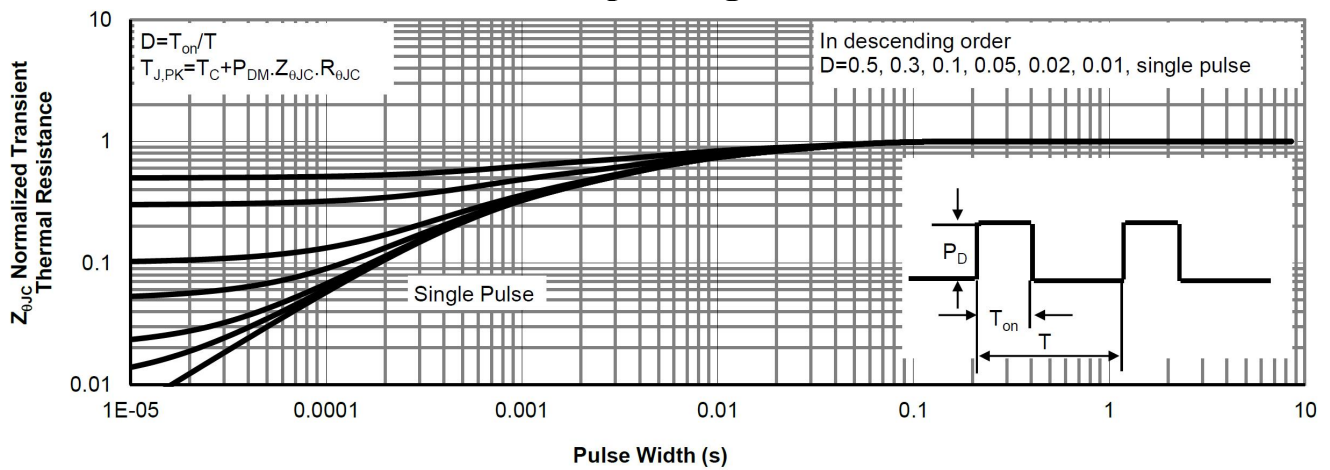
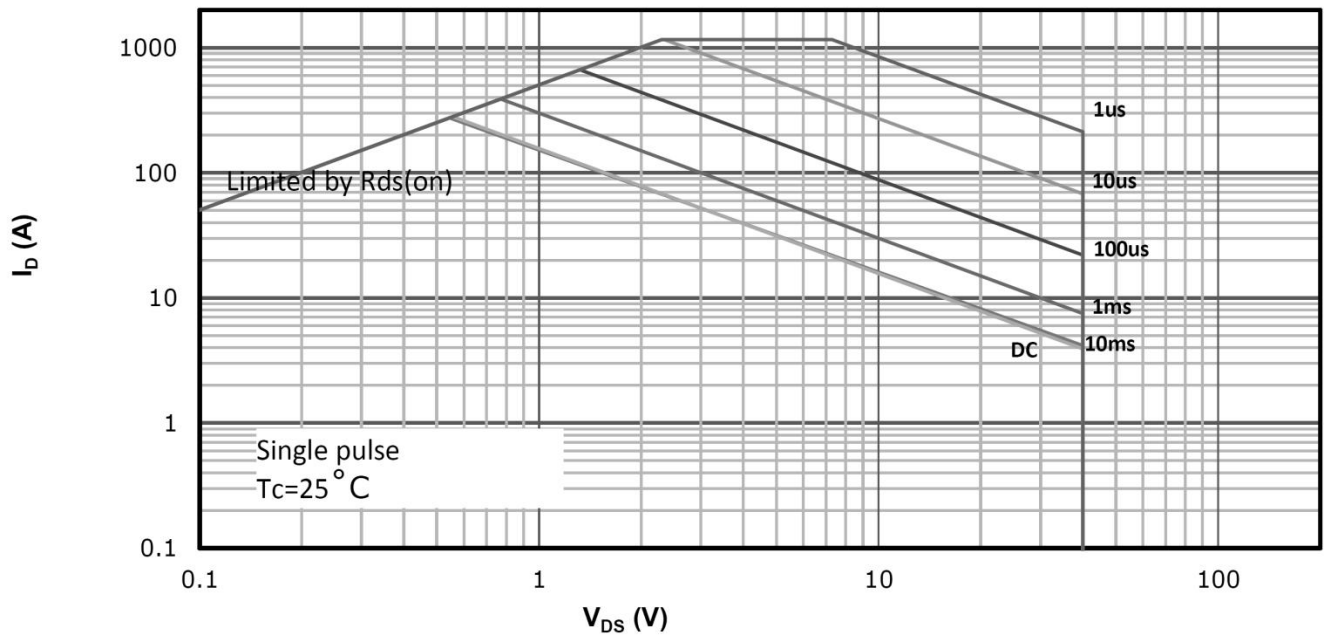
$R_{DS(on)}$ vs. Temperature

$V_{GS(th)}$ vs. Temperature



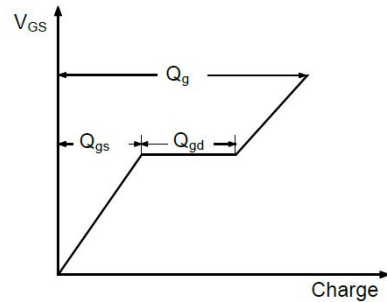
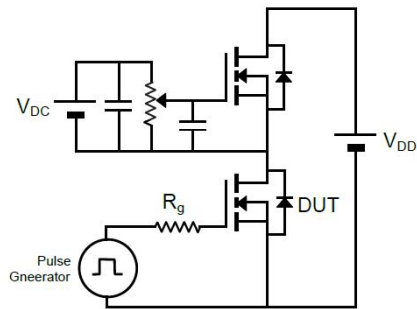
Power Dissipation

Drain Current Derating

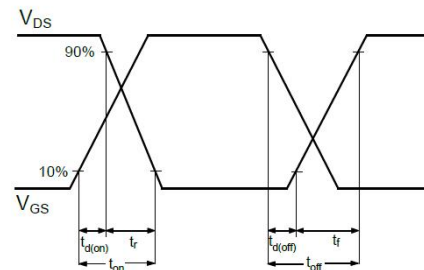
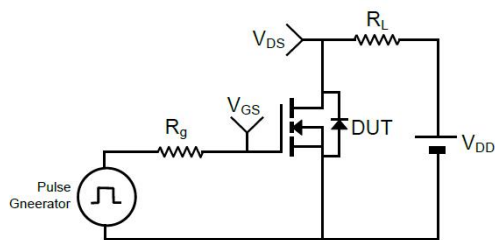


Test Circuit

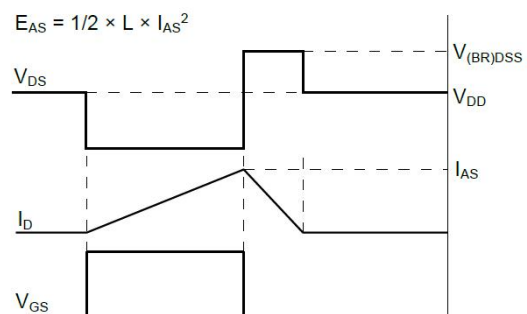
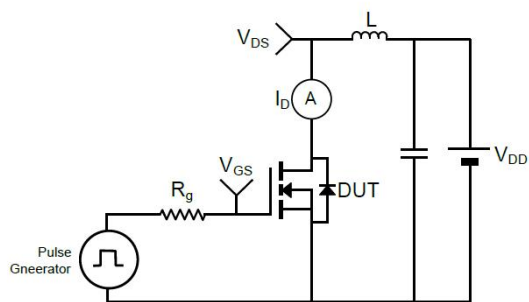
Gate Charge



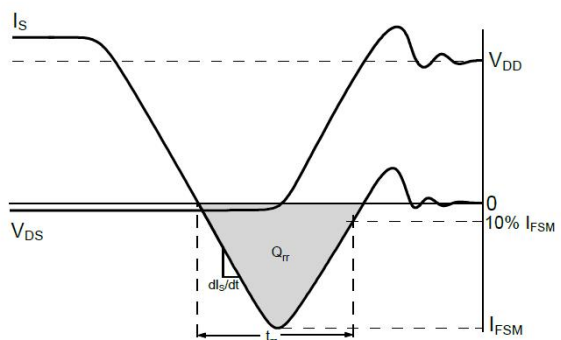
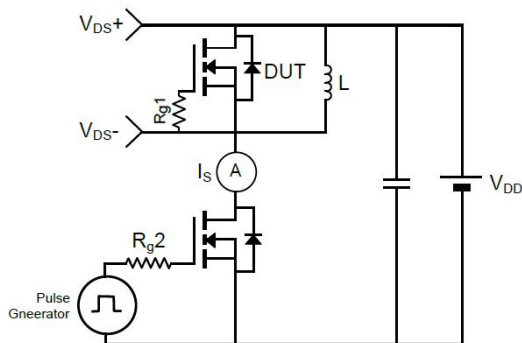
Resistive Load Switching Time

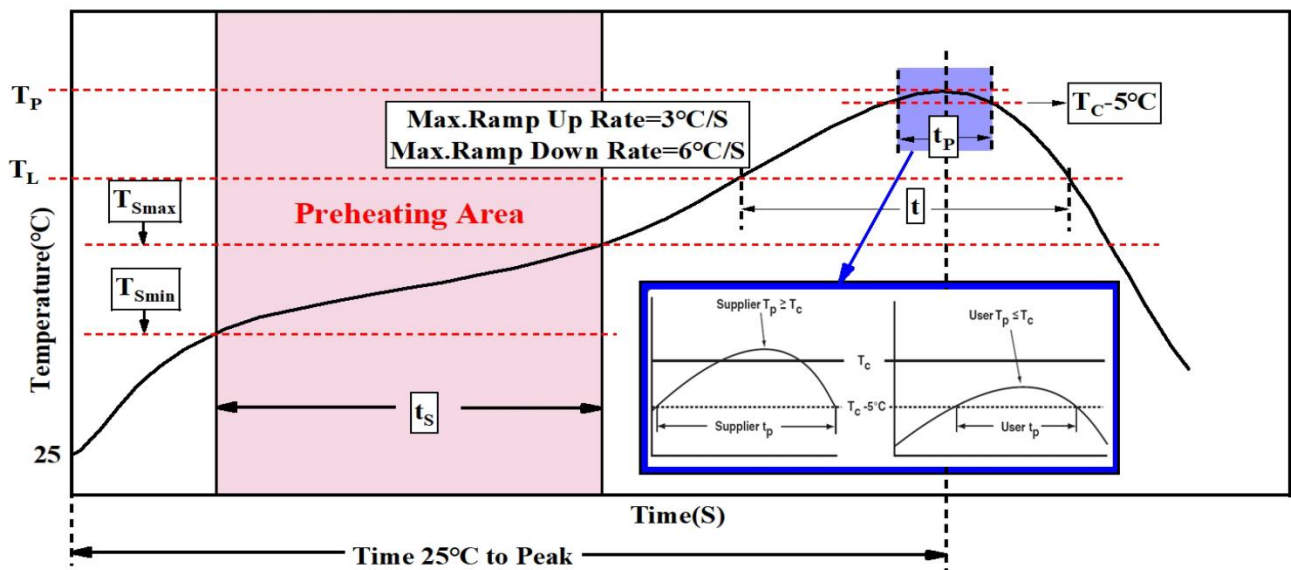


Un-clamped Inductive Load Switching



Drain-Source Body Diode Reverse Recovery



Temperature Profile for IR Reflow Soldering


Profile Feature	Sn-Pb Eutectic Assembly	Pb-Free Assembly
Preheat & Soak		
Temperature min (T _{smin})	100°C	150°C
Temperature max (T _{smax})	150°C	200°C
Time (T _{smin} to T _{smax}) (t _s)	60-120 seconds	60-120 seconds
Average ramp-up rate (T _{smax} to T _p)	3 °C/second max.	3°C/second max.
Liquidous temperature (T _L)	183 °C	217°C
Time at liquidous (t _L)	60-150 seconds	60-150 seconds
Peak package body Temperature e (T _p)*	See Classification Temp in table 1	See Classification Temp in table 2
Time (t _p)** within 5°C of the specified classification temperature (T _c)	20** seconds	30** seconds
Average ramp-down rate (T _p to T _{smax})	6 °C/second max.	6 °C/second max.
Time 25°C to peak temperature	6 minutes max.	8 minutes max.
* Tolerance for peak profile Temperature (T _p) is defined as a supplier minimum and a user maximum. ** Tolerance for time at peak profile temperature (t _p) is defined as a supplier minimum and a user maximum		

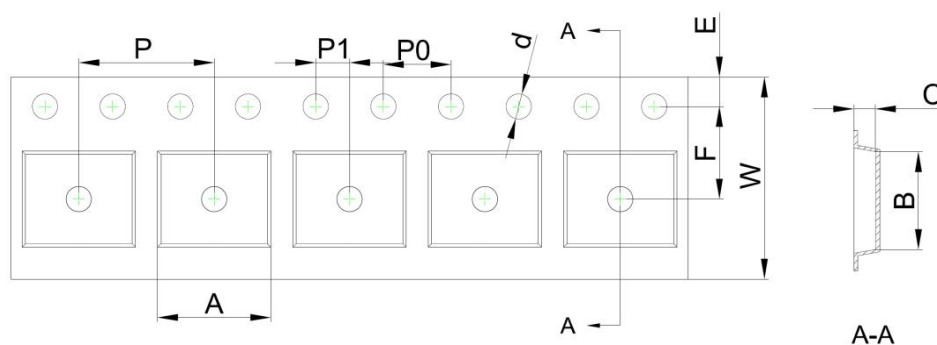
Table 1. SnPb Eutectic Process – Classification Temperatures (T_c)

Package Thickness	Volume mm ³ <350	Volume mm ³ ≥350
<2.5 mm	235 °C	220 °C
≥2.5 mm	220 °C	220 °C

Table 2. Pb-free Process – Classification Temperatures (T_c)

Package Thickness	Volume mm ³ <350	Volume mm ³ 350-2000	Volume mm ³ >2000
<1.6 mm	260 °C	260 °C	260 °C
1.6 mm – 2.5 mm	260 °C	250 °C	245 °C
≥2.5 mm	250 °C	245 °C	245 °C

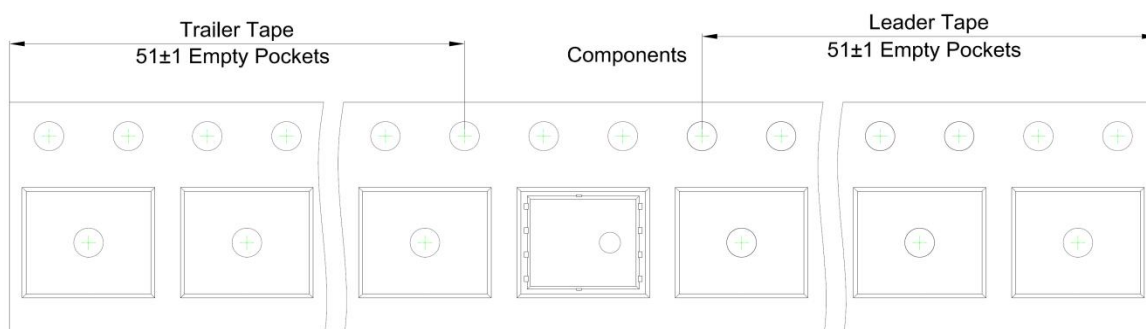
PDFN5X6-8L Embossed Carrier Tape



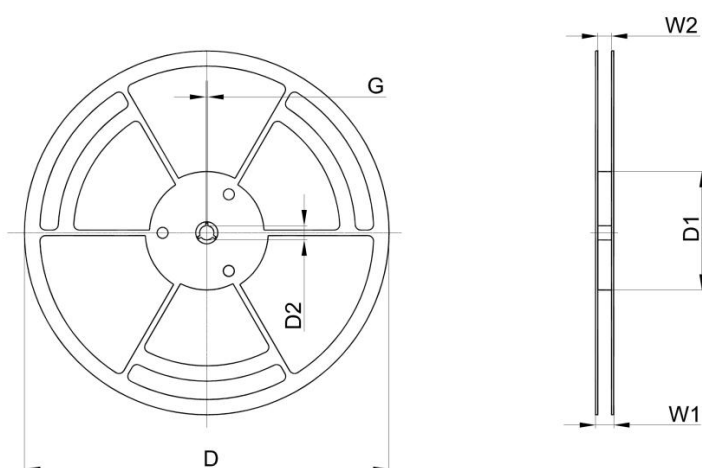
Dimensions are in millimeter

Pkg type	A	B	C	d	E	F	P0	P	P1	W
PDFN5X6-8L	6.30	5.30	1.10	Φ1.50	1.75	5.50	4.00	8.00	2.00	12.00

PDFN5X6-8L Tape Leader and Trailer



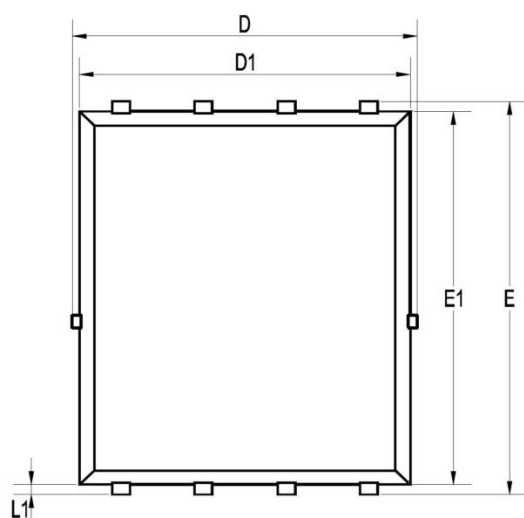
PDFN5X6-8L Reel



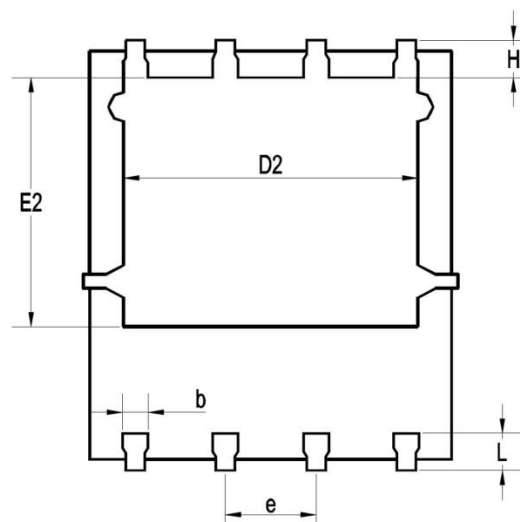
Dimensions are in millimeter

Reel Option	D	D1	D2	G	W1	W2
13"Dia	Ø330.00	100.00	13.00	1.90	17.60	12.40

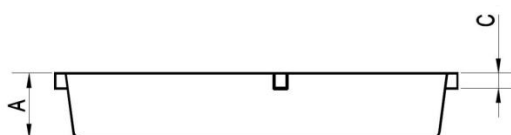
REEL	Reel Size	Box	Box Size(mm)	Carton	Carton Size(mm)
5,000 pcs	13 inch	5,000 pcs	340×336×29	50,000 pcs	353×346×365

PDFN5X6-8L Package Information


Top View
[顶视图]



Bottom View
[背视图]



Side View
[侧视图]

Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.900	1.200	0.035	0.047
b	0.330	0.510	0.013	0.020
C	0.110	0.340	0.004	0.013
D	4.700	5.260	0.185	0.207
D1	4.700	5.100	0.185	0.201
D2	3.560	4.500	0.140	0.177
E	5.750	6.250	0.226	0.246
E1	5.600	6.000	0.220	0.236
E2	3.180	3.660	0.125	0.144
e	1.170	1.370	0.046	0.054
L	0.350	0.750	0.014	0.030
L1	0.000	0.200	0.000	0.008
H	0.350	0.710	0.014	0.028